

UTC2SA684 PNP EPITAXIAL PLANAR TRANSISTOR

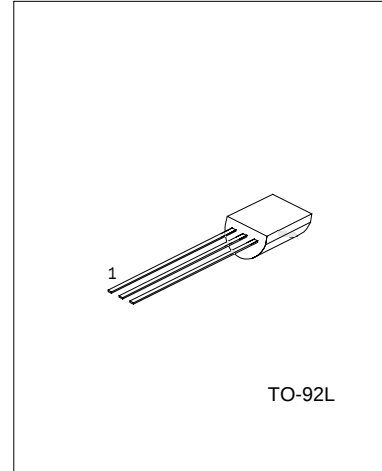
PNP EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The UTC 2SA684 is power amplifier and driver.

FEATURES

- *Automatic insertion by radial taping possible.
- *Complementary pair with 2SC1384



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CE0}	50	V
Emitter-Base Voltage	V _{EB0}	5	V
Peak Collector Current	I _{cp}	1.5	A
Collector Current(DC)	I _c	1	A
Collector Dissipation(Ta=25°C)	P _c	1	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Collector-Base Voltage	V _{CB0}	I _c =10μA, I _E =0	60			V
Collector-Emitter Voltage	V _{CE0}	I _c =2mA, I _B =0	50			V
Emitter-Base Voltage	V _{EB0}	I _E =10μA, I _c =0	5			V
DC Current Gain	h _{FE1} h _{FE2}	V _{CE} =10V, I _c =500mA V _{CE} =5V, I _B =1A	85 50		340	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c =0.5A, I _B =50mA		0.2	0.4	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c =0.5A, I _B =50mA		0.85	1.2	V
Current Gain Bandwidth Product	f _T	V _{CE} =10V, I _B =50mA, f=200MHz		200		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		20	30	pF

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CLASSIFICATION OF hFE

RANK	Q	R	S
RANGE	85-170	120-240	170-340

TYPICAL PERFORMANCE CHARACTERISTICS